POWER MOSFETs | IN A NUTSHELL

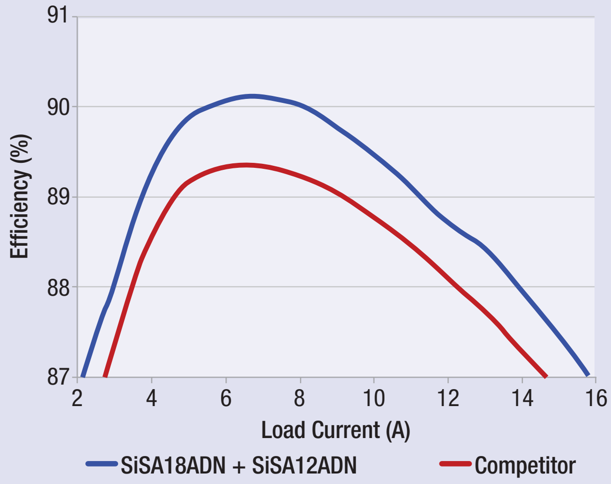
Low Voltage TrenchFET®

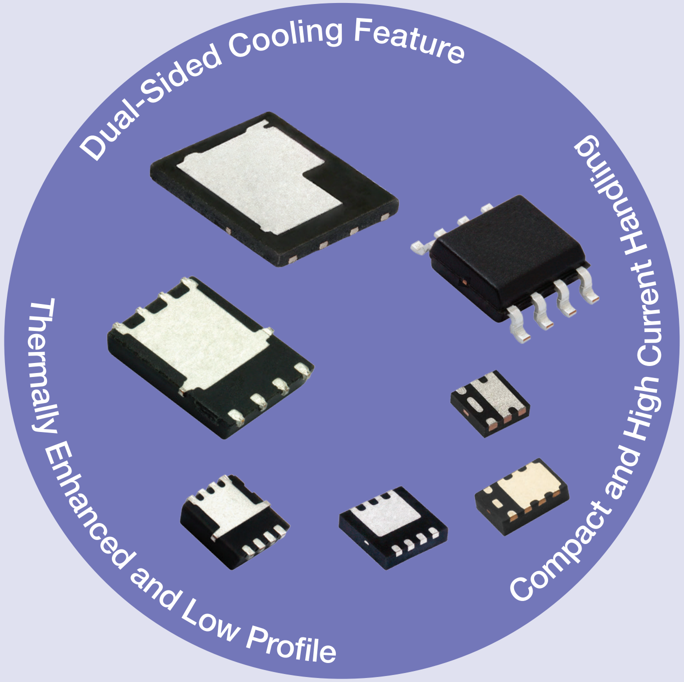
Industry's lowest $R_{DS(on)}$ n-channel MOSFETs in an array of advanced packages

- Less than 0.58 mΩ
- Breakdown voltages: 25 V to 30 V
- Excellent R_{DS} - Q_g FOM improves efficiency for switch-mode power supplies

TYPICAL EFFICIENCY IMPROVEMENT EXPECTATION

Benchmarking condition 12.9 V_{IN}, 1.8 V_{OUT}, 800 kHz



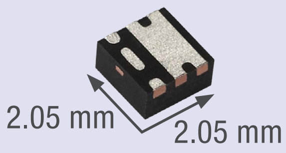


Higher efficiency

Increased power density

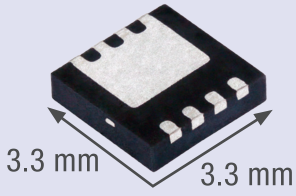
Space-saving packages

SiA468DJ



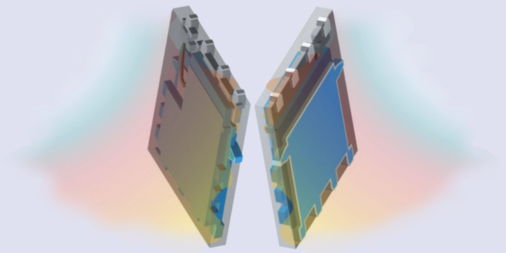
Up to 37.8 A continuous I_D

SiSS02DN



< 1.2 mΩ, 10.89 mm^2 footprint

Dual-sided cooling feature



APPLICATIONS

CONSUMER ELECTRONICS

DRONES

COMPUTERS

SERVERS

TELECOM EQUIPMENT

For Technical Questions: pmostechsupport@vishay.com